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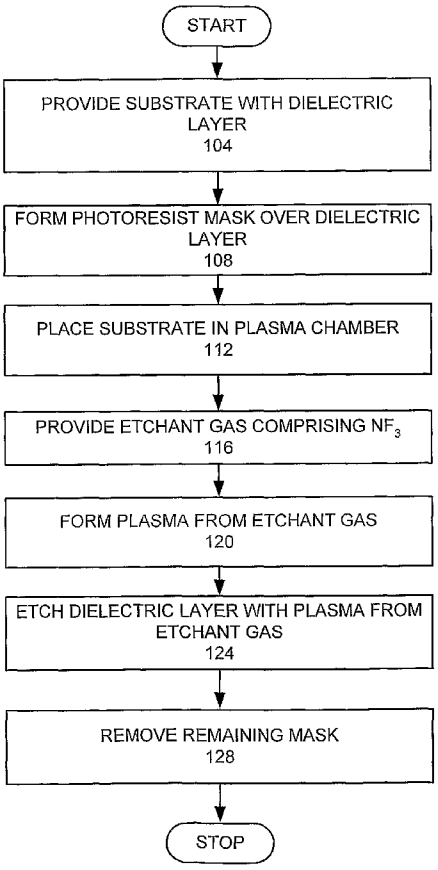
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(54) Title: ETCH WITH PHOTORESIST MASK



(57) Abstract: A method for etching a dielectric layer over a substrate is provided. A photoresist mask is formed over the dielectric layer. The substrate is placed in a plasma processing chamber. An etchant gas comprising NF_3 is provided into the plasma chamber. A plasma is formed from the NF_3 gas. The dielectric layer is etched through the photoresist mask with the plasma from the NF_3 gas.

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